

The following listing of claims will replace all prior versions, and listings, of claims in the present application.

LISTING OF THE CLAIMS:

1. (Currently Amended) A varactor structure comprising:

a semiconductor substrate including a subcollector of a second conductivity type located below an upper region of said semiconductor substrate and a semiconductor layer of a first conductivity type beneath the subcollector, said first conductivity type is different from said second conductivity;

a well region located in said upper region of said semiconductor substrate, wherein said well region includes outer well regions of said second conductivity type and an inner well region of said first conductivity type, each well of alternating conductivity type of said well region is separated at an upper surface by an isolation region and [[each outer]] the inner well region has an upper surface which includes source and drain regions, wherein the source and drain regions are separated from the outer well regions by the isolation region comprising a dielectric material [[a source/drain region]]; and

a field effect transistor having at least a gate conductor of said first conductivity type located above said inner well region, the outer well regions and the inner well region are in contact with the subcollector having the second conductivity type, wherein said each well of alternating conductivity type of said well region extends beneath the isolation region to the subcollector such that neighboring well regions are in contact with each other along an entire depth of each well region, wherein the subcollector continuously extends through the outer well region and the inner well region of the semiconductor substrate.

2. (Original) The varactor structure of Claim 1 wherein said first conductivity type comprises a p-type dopant and second conductivity type comprises a n-type dopant.

3. (Original) The varactor structure of Claim 1 wherein said first conductivity type comprises a n-type dopant and said second conductivity type comprises a p-type dopant.

4. (Cancelled).

5. (Cancelled).

6. (Previously Presented) The varactor structure of Claim 1 wherein said upper region of said semiconductor substrate comprises an epitaxial semiconductor layer.

7. (Original) The varactor structure of Claim 1 wherein said field effect transistor further comprises a gate dielectric located beneath said gate conductor, a hard mask located on said gate conductor, at least one spacer located on sidewalls of said gate conductor and abutting source/drain regions.

8. (Original) The varactor structure of Claim 1 wherein said gate conductor comprises polysilicon.

9. (Currently Amended) A varactor structure comprising:

a p-type semiconductor substrate including an n-type subcollector located below an upper region of said semiconductor substrate and a p-type semiconductor layer beneath the n-type subcollector;

a well region located in said upper region of said semiconductor substrate, wherein said well region includes outer N-well regions and an inner P-well region, each well of alternating conductivity type of said well region is separated at an upper surface by an isolation region and [[each outer]] the inner well region has an upper surface which includes source and drain regions, wherein the source and drain regions are separated from the outer well regions by the isolation region comprising a dielectric material [[a source/drain region]]; and

a field effect transistor having at least a p-type gate conductor located above said inner P-well region, the outer N-well regions and the inner P-well region are in contact with the n-type

subcollector, wherein the outer N-well regions and the inner P-well region extend beneath the isolation region to the n-type subcollector such that neighboring well regions are in contact with each other along an entire depth of each well region, wherein the n-type subcollector continuously extends through the outer N-well regions and the inner P-well region.

10. (Cancelled).

11. (Cancelled).

12. (Original) The varactor structure of Claim 9 wherein said upper region of said semiconductor substrate comprises an epitaxial semiconductor layer.

13. (Original) The varactor structure of Claim 9 wherein said field effect transistor further comprises a gate dielectric located beneath said gate conductor, a hard mask located on said gate conductor, at least one spacer located on sidewalls of said gate conductor and abutting source/drain regions.

14. (Original) The varactor structure of Claim 9 wherein said gate conductor comprises polysilicon.

15. (Withdrawn) A method of fabricating a varactor structure comprising the steps of:
providing a structure that comprises a semiconductor substrate of a first conductivity type;

forming a plurality of isolation regions in said upper region of said substrate;

forming a well region in said upper region of said substrate, wherein said well region includes outer well regions of a second conductivity type that differs from said first conductivity type and an inner well region of said first conductivity type, each well of said well region is separated at an upper surface by an isolation region; and

forming a field effect transistor having at least a gate conductor of said first conductivity type above said inner well region, wherein a doped region of the second conductivity type is formed into an upper region of said substrate prior to, or immediately after forming said plurality of isolation regions.

16. (Withdrawn) The method of Claim 15 wherein said first conductivity type comprises a p-type dopant and second conductivity type comprises an n-type dopant.

17. (Withdrawn) The method of Claim 15 wherein said first conductivity type comprises a n-type dopant and said second conductivity type comprises a p-type dopant.

18. (Withdrawn) The method of Claim 15 wherein said doped region comprises a subcollector or an isolation well that is formed by ion implantation.

19. (Withdrawn) The method of Claim 15 wherein said upper region of said substrate comprises an epitaxial grown semiconductor layer which is formed after forming the doped region.

20. (Withdrawn) The method of Claim 15 wherein forming said well region comprises masked ion implantation processes.